MJE15034 (NPN), MJE15035 (PNP)

Complementary Silicon Plastic Power Transistors

TO-220, NPN & PNP Devices

Complementary silicon plastic power transistors are designed for use as high–frequency drivers in audio amplifiers.

Features

- High Current Gain Bandwidth Product
- TO-220 Compact Package
- Epoxy meets UL 94 V-0 @ 0.125 in
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit	
Collector-Emitter Voltage	V _{CEO}	350	Vdc	
Collector-Base Voltage	V _{CB}	350	Vdc	
Emitter-Base Voltage	V _{EB}	V _{EB} 5.0		
Collector Current – Continuous	Ι _C	4.0	Adc	
Collector Current – Peak	I _{CM}	8.0	Adc	
Base Current	I _B	1.0	Adc	
Total Power Dissipation @ T _C = 25°C Derate above 25°C	PD	50 0.40	W W/°C	
Total Power Dissipation @ T _A = 25°C Derate above 25°C	PD	2.0 0.016	W W/°C	
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C	
ESD – Human Body Model	HBM	3B	V	
ESD – Machine Model	MM	С	V	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	R_{\thetaJC}	2.5	°C/W
Thermal Resistance, Junction-to-Ambient	R_{\thetaJA}	62.5	°C/W

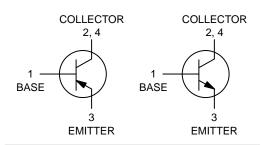


ON Semiconductor®

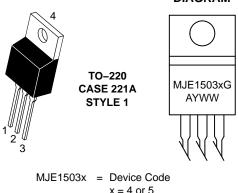
www.onsemi.com

4.0 AMPERES POWER TRANSISTORS COMPLEMENTARY SILICON 350 VOLTS, 50 WATTS

COMPLEMENTARY







		x = + 01 J
А	=	Location Code
Y	=	Year
WW	=	Work Week
G	=	Pb–Free Package

ORDERING INFORMATION

Device	Package	Shipping
MJE15034G	TO–220 (Pb–Free)	50 Units / Rail
MJE15035G	TO–220 (Pb–Free)	50 Units / Rail

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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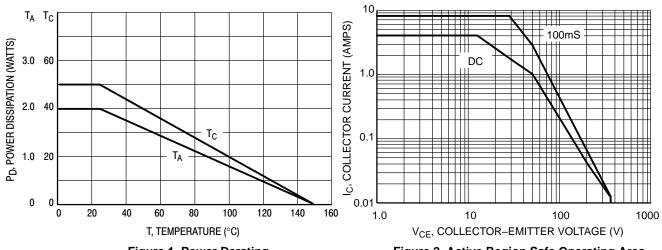
ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Voltage (Note 1)	$(I_{C} = 10 \text{ mAdc}, I_{B} = 0)$	V _{CEO(sus)}	350	-	Vdc
Collector Cutoff Current	$(V_{CB} = 350 \text{ Vdc}, I_E = 0)$	I _{CBO}	-	10	μAdc
Emitter Cutoff Current	$(V_{BE} = 5.0 \text{ Vdc}, I_{C} = 0)$	I _{EBO}	-	10	μAdc
ON CHARACTERISTICS (Note 1)					
DC Current Gain		h _{FE}	100 100 50 10		-
Collector-Emitter Saturation Voltage	$(I_{C} = 1.0 \text{ Adc}, I_{B} = 0.1 \text{ Adc})$	V _{CE(sat)}	-	0.5	Vdc
Base-Emitter On Voltage	$(I_{C} = 1.0 \text{ Adc}, V_{CE} = 5.0 \text{ Vdc})$	V _{BE(on)}	-	1.0	Vdc
DYNAMIC CHARACTERISTICS			-		•

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.

2. $f_T = |h_{fe}| \bullet f_{test}$.







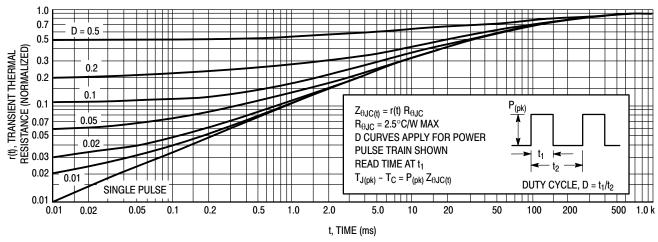
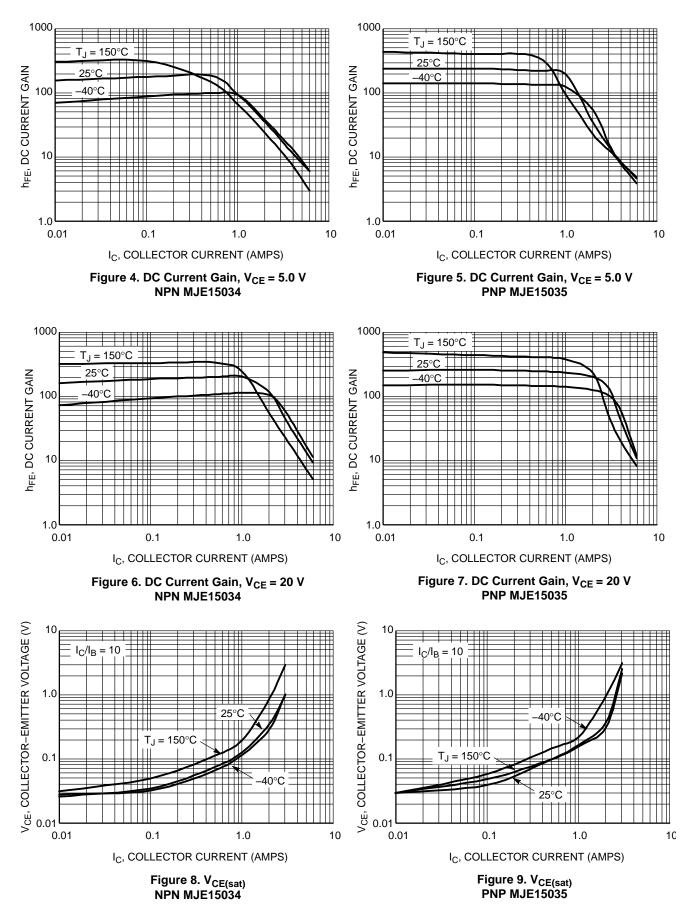
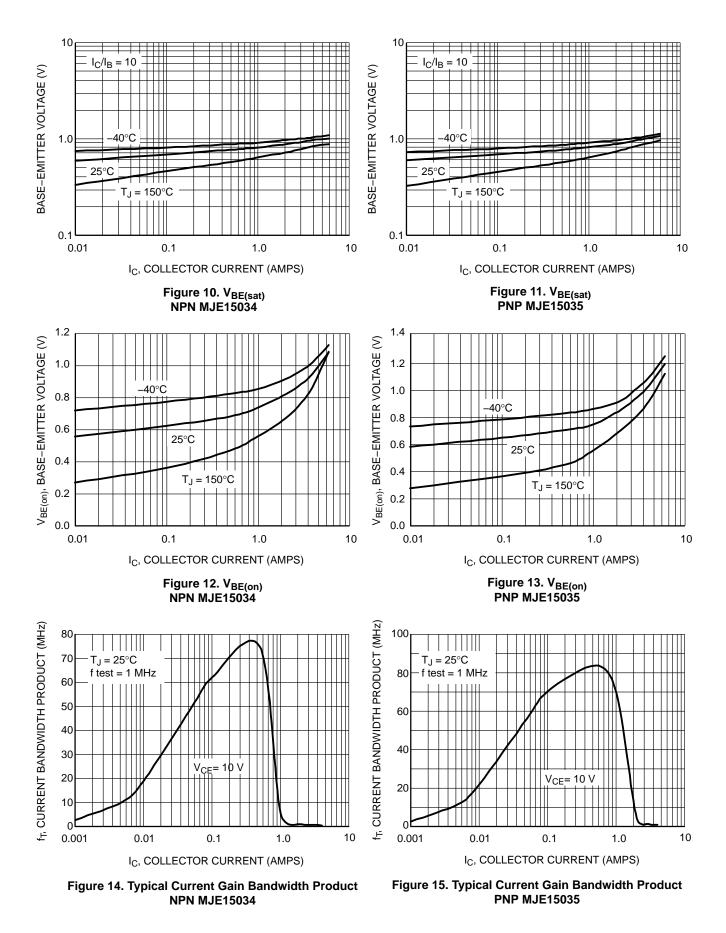


Figure 3. Thermal Response

MJE15034 (NPN), MJE15035 (PNP)



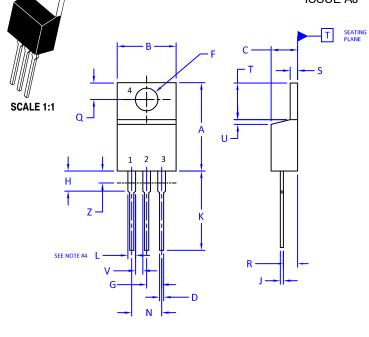
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DATE 05 NOV 2019



TO-220 CASE 221A-09 ISSUE AJ



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.

2. CONTROLLING DIMENSION: INCHES

3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

4. MAX WIDTH FOR F102 DEVICE = 1.35MM

	INCHES		MILLIME	ETERS	
DIM	MIN.	MAX.	MIN.	MAX.	
А	0.570	0.620	14.48	15.75	
В	0.380	0.415	9.66	10.53	
С	0.160	0.190	4.07	4.83	
D	0.025	0.038	0.64	0.96	
F	0.142	0.161	3.60	4.09	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.161	2.80	4.10	
J	0.014	0.024	0.36	0.61	
К	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
Ν	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.41	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
V	0.045		1.15		
Z		0.080		2.04	

STYLE 1: PIN 1. 2. 3. 4.	COLLECTOR EMITTER	STYLE 2: PIN 1. 2. 3. 4.	EMITTER	3.	CATHODE ANODE GATE ANODE	STYLE 4: PIN 1. 2. 3. 4.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE MAIN TERMINAL 2
STYLE 5: PIN 1. 2. 3. 4.	DRAIN SOURCE	2. 3.	ANODE CATHODE ANODE CATHODE	2. 3.	CATHODE ANODE CATHODE ANODE	STYLE 8: PIN 1. 2. 3. 4.	••••••
STYLE 9: PIN 1. 2. 3. 4.	COLLECTOR EMITTER	STYLE 10: PIN 1. 2. 3. 4.	GATE SOURCE DRAIN	STYLE 11: PIN 1. 2. 3. 4.	DRAIN SOURCE GATE	STYLE 12 PIN 1. 2. 3. 4.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE NOT CONNECTED

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